

SD0103WS

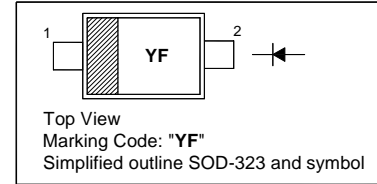
SILICON SCHOTTKY BARRIER DIODE

Features

- Low forward voltage drop and suitable for high efficiency rectifying
- Ultra small resin package is suitable for high density surface mounting and high speed assembly

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

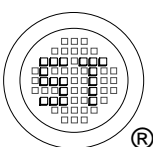


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	30	V
Mean Rectifying Current	I_O	100	mA
Non-Repetitive Peak Forward Surge Current (8.3 ms Single Half Sine Wave)	I_{FSM}	1	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	0.44	V
Reverse Current at $V_R = 30\text{ V}$	I_R	50	μA



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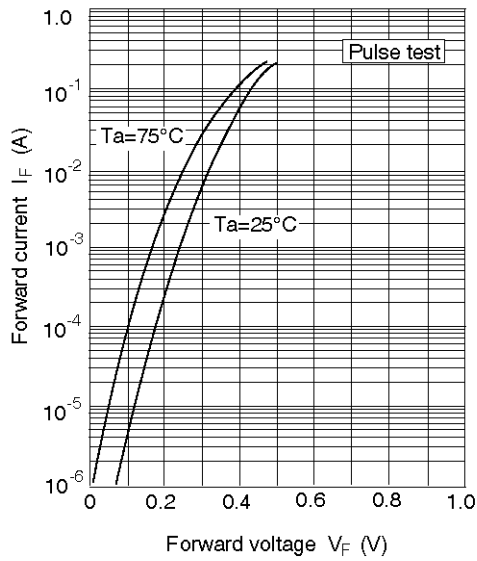


Fig.1 Forward current Vs. Forward voltage

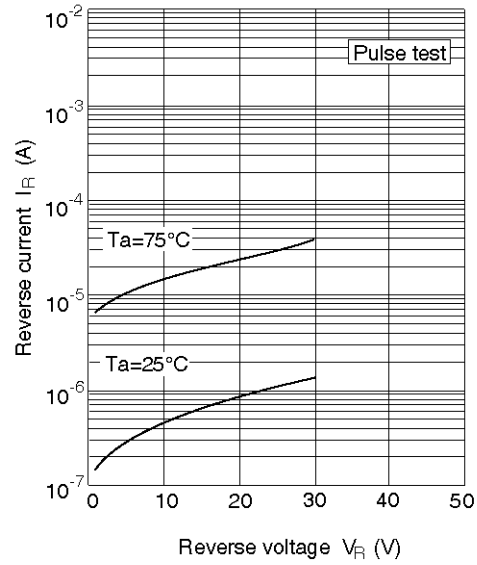


Fig.2 Reverse current Vs. Reverse voltage

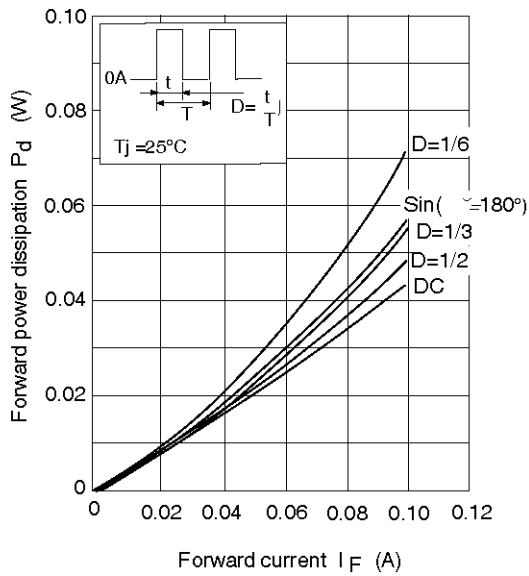


Fig.3 Forward power dissipation Vs. Forward current

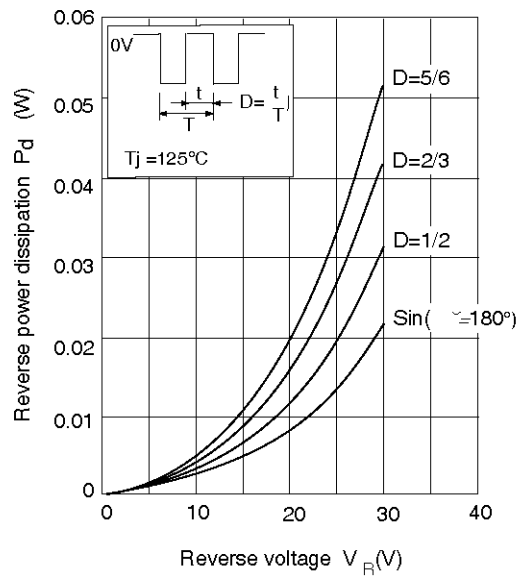
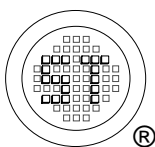


Fig.4 Reverse power dissipation Vs. Reverse voltage

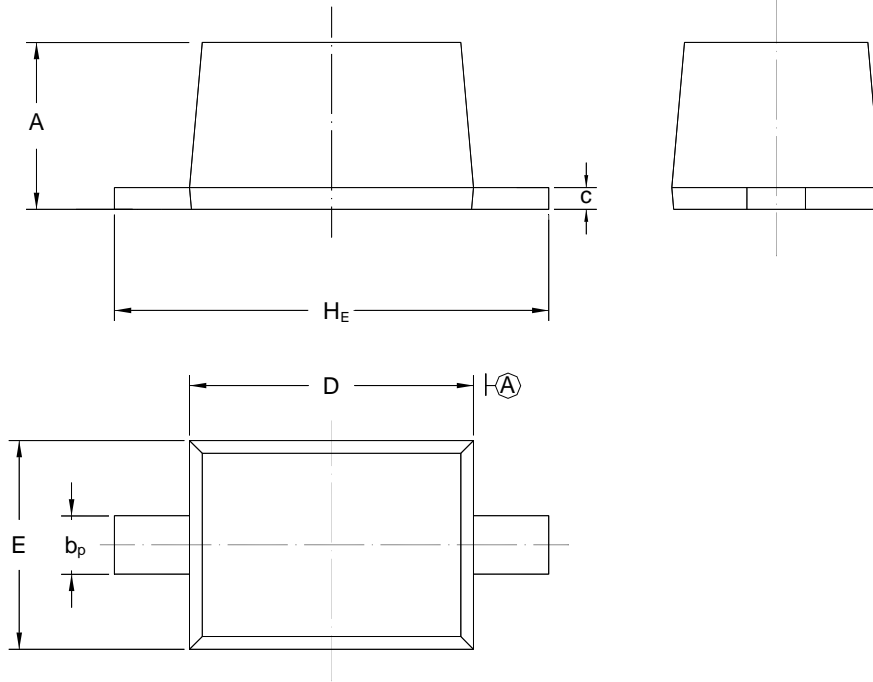


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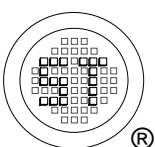
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b _p	C	D	E	H _E
mm	1.10 0.80	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30



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